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 Low Quiescent Supply Current of 20 μA Optimized for Low-Power/Battery-Operated 		ACKAGE VIEW)
Applications		20 GNDS
 Two Input Control Lines for Reduced Microcontroller Overhead 	V _{CC} [] 2 IN1 [] 3	19 V _{CC} 18 STATUS2
 Internal Current Shutdown of 5 A 		17 V _{CC}
 40 V Load Dump Rating 	OUT1 [] 5	16 OUT2
Integrated Fault Protection and Diagnostics	OUT1 🛮 6	15 OUT2
CMOS Compatible Schmitt Trigger Inputs		
for High Noise Immunity	IN2 [] 8 GND [] 9	13 STATUS1 12 GND
description	GNDS [10	12 GND

d

The TPIC0108B is a PWM control intelligent H-bridge designed specifically for dc motor applications. The device provides forward, reverse, and brake modes of operation. A logic supply voltage of 5 V is internally derived from V_{CC}.

The TPIC0108B has an extremely low $r_{DS(on)}$, 280 m Ω typical, to minimize system power dissipation. The control inputs (IN1 and IN2) greatly simplify the microcontroller overhead requirement. The device has a low quiescent supply current of 20 µA to suit a wide range of automotive and industrial battery-operated applications.

The TPIC0108B provides protection against over-voltage, over-current, over-temperature, and cross conduction faults. Fault diagnostics can be obtained by monitoring the STATUS1 and STATUS2 terminals and the two input control lines. STATUS1 is an open-drain output suitable for wired-or connection. STATUS2 is a push-pull output that provides a latched status output. Under-voltage protection ensures that the outputs, OUT1 and OUT2, will be disabled when V_{CC} is less than the under-voltage detection voltage V_(UVCC).

The TPIC0108B is designed using TI's LinBiCMOS™ process. LinBiCMOS allows the integration of low power CMOS structures, precision bipolar cells, and low impedance DMOS transistors.

The TPIC0108B is offered in a 20-pin thermally enhanced small-outline package (DWP) and is characterized for operation over the operating case temperature of -40°C to 125°C.

IN1	IN2	OUT1	OUT2	MODE						
0	0	Z	Z	Quiescent supply current mode						
0	1	LS	HS	Motor turns clockwise						
1	0	HS	LS	Motor turns counter clockwise						
1	1	HS	HS	Brake, both HSDs turned on hard						

ELINCTION TABLE



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

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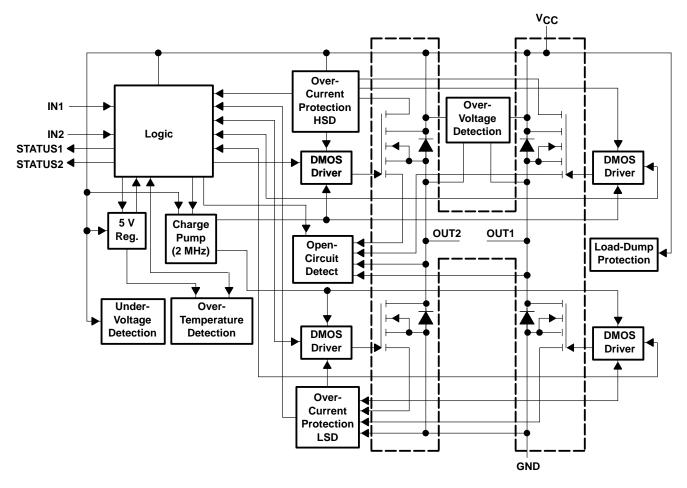
PRODUCTION DATA information is current as of publication date. Products conform to specifications per the terms of Texas Instruments standard warranty. Production processing does not necessarily include testing of all parameters.



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block schematic



Terminal Functions

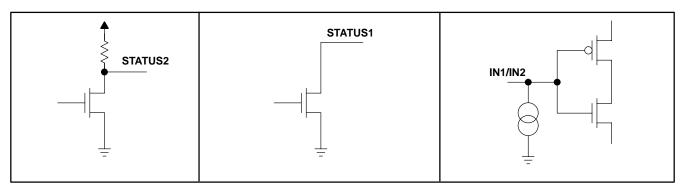
TERM	IINAL	1/0	DESCRIPTION
NAME	NO.	1/0	DESCRIPTION
GND	7, 9, 12, 14	I	Power ground
GNDS	1, 10, 11, 20	I	Substrate ground
IN1	3	I	Control input
IN2	8	I	Control input
OUT1	5, 6	0	Half-H output. DMOS output
OUT2	15, 16	0	Half-H output. DMOS output
STATUS1	13	0	Status output
STATUS2	18	0	Latched status output
Vcc	2, 4, 17, 19	Ι	Supply voltage

NOTE: It is mandatory that all four ground terminals plus at least one substrate terminal are connected to the system ground. Use all V_{CC} and OUT terminals.



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schematics of inputs and outputs



absolute maximum ratings over operating case temperature range (unless otherwise noted)[†]

Power supply voltage range, V _{CC}	–0.3 V to 33 V
Logic input voltage range, V _{IN}	–0.3 V to 7 V
Load dump (for 400 ms; $T_C = 25^{\circ}C$)	40 V
Status output voltage range, $V_{O(status)}$ Continuous power dissipation, $T_C = 25^{\circ}C$	–0.3 V to 7 V
Continuous power dissipation, $T_C = 25^{\circ}C$	1.29 W
Storage temperature range, T _{stg}	–55°C to 150°C
Maximum junction temperature, T _J	150°C

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

DISSIPATION RATING TABLE

T _A ≤ 25°C	DERATING FACTOR	T _A = 70°C	T _A = 125°C
POWER RATING	ABOVE T _A = 25°C	POWER RATING	POWER RATING
1.29 W	0.0104 W/°C	0.82 W	

recommended operating conditions

	MIN	MAX	UNIT
Supply voltage, V _{CC}	6	18	V
Operating case temperature, T _C	-40	125	°C
Switching frequency, fPWM		2	kHz



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electrical characteristics over recommended operating case temperature range and $V_{CC} = 5 V$ to 6 V (unless otherwise noted)

	PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
		LSD	TJ = 25°C			550	
	Static drain-source on-resistance (per transistor)	LSD	TJ = 150°C			850	mΩ
rDS(on)	I _(BR) = 1 A	HSD	TJ = 25°C			600	
			TJ = 150°C			870	mΩ
I(QCD)	Open circuit detection current			10	40	100	mA
V(UVCC(OFF))	Under voltage detection on V _{CC} , switch off voltage)	See Note 1			5	V
V(UVCC(ON))	Under voltage detection on V_{CC} , switch on voltage	Inder voltage detection on V _{CC} , switch on voltage				5.2	V
V _(STL)	STATUS low output voltage		I_{O} = 100 μ A, See Note 1			0.8	V
V(ST2H)	STATUS2 high output voltage		I_{O} = 20 μ A, See Note 1	3		5.4	V
I(ST(OFF))	STATUS output leakage current		V _(ST) = 5 V, See Note 1			5	μA
VIL	Low level logic input voltage			-0.3		0.5	V
VIH	High level logic input voltage			3.6		7	V
ΔVI	Hysteresis of input voltage			0.3			V
Чн	High level logic input current		V _{IH} = 3.5 V	2	10	50	μA

NOTE 1: The device functions according to the function table for V_{CC} between V_(UVCC) and 5 V (no parameters specified). STATUS outputs are not defined for V_{CC} less than V_(UVCC).



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electrical characteristics over recommended operating case temperature and supply voltage ranges (unless otherwise noted) (see Note 2)

	PARAMETER		TES	T CONDITIONS	MIN	TYP	MAX	UNIT
			Т _Ј = 25°С	$V_{CC} = 6 V \text{ to } 9 V$			380	
		LSD	1J=25 C	V _{CC} = 9 V to 18 V		280	340	mΩ
		LOD	T _J = 150°C	$V_{CC} = 6 V \text{ to } 9 V$			620	11152
	Static drain-source on-resistance		1] = 150 C	V _{CC} = 9 V to 18 V		400	560	
^r DS(on)	(per transistor) I _{BR} = 1 A		Тј = 25°С	$V_{CC} = 6 V \text{ to } 9 V$			430	
		HSD	1 j = 23 C	V _{CC} = 9 V to 18 V		280	340	mΩ
		1130	Тј = 150°С	$V_{CC} = 6 V \text{ to } 9 V$			640	11152
			1J = 150 C	V _{CC} = 9 V to 18 V		400	560	
I(QB)	Quiescent battery current		TJ = 25°C	V _{CC} = 13.2 V			20	μA
I(QCD)	Open circuit detection current				10	40	100	mA
T _{SDS}	Static thermal shutdown temperatur	e	See Notes 3 and 4		140			°C
T _{SDD}	Dynamic thermal shutdown tempera	tdown temperature S		See Notes 3 and 5				°C
100	Current shutdown limit		$V_{CC} = 6 V \text{ to } 9 V$	/	4.8		7.5	А
ICS	Current shatdown innit		V _{CC} = 9 V to 18	V	5		7.5	A
I(CON)	Continuous bridge current		T _J = 125°C, Ope (see Figure 1)	erating lifetime 10,000 hours,			3	А
V(OVCC)	Over voltage detection on V_{CC}				27		36	V
V(STL)	STATUS low output voltage		l _O = 100 μA				0.8	V
V(ST2H)	STATUS2 high output voltage		IO = 20 μA		3.9		5.4	V
I(ST(OFF))	STATUS output leakage current		V _(ST) = 5 V				5	μΑ
VIL	Low level logic input voltage				-0.3		0.8	V
VIH	High level logic input voltage				3.6		7	V
ΔVI	Hysteresis of input voltage				0.3			V
Ιн	High level logic input current		V _{IH} = 3.5 V		2	10	50	μA

NOTES: 2. The device functions according to the function table for V_{CC} between 18 V and V_(OVCC), but only up to a maximum supply voltage of 33 V (no parameters specified). Exposure beyond 18 V for extended periods may affect device reliability.

3. Exposure beyond absolute-maximum-rated condition of junction temperature may affect device reliability.

4. No temperature gradient between DMOS transistor and temperature sensor.

5. With temperature gradient between DMOS transistor and temperature sensor in a typical application (DMOS transistor as heat source).

switching characteristics over recommended operating case temperature and supply voltage ranges (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
+	High-side driver turn-on time	$\sqrt{2}$			100	
^t out(on)	Low-side driver turn-on time	V _{DS(on)} <1 V at 1 A, V _{CC} = 13.2 V			100	μs
CD.	Slew rate, low-to-high sinusoidal ($\delta V / \delta t$)	$V_{CC} = 13.2 \text{ V},$ $I_{O} = 1 \text{ A resistive load}$	1		6	V/µs
SR	Slew rate, high-to-low sinusoidal ($\delta V/\delta t$)	$V_{CC} = 13.2 \text{ V},$ $I_O = 1 \text{ A resistive load}$	1		6	v/µs
^t d(QCD)	Under current spike duration to trigger open circuit detection	$V_{CC} = 5 V \text{ to } 18 V$	1		10	ms
^t d(CS)	Delay time for over current shutdown		5	10	25	μs



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thermal resistance

	PARAMETER	MIN	MAX	UNIT
$R_{\theta JA}$	Junction-to-ambient thermal resistance		97	°C/W
$R_{\theta JC}$	Junction-to-case thermal resistance		5	°C/W

PARAMETER MEASUREMENT INFORMATION

Maximum continuous bridge current versus time based on 50 FITs at 100,000 hours operating life (90% confidence model)

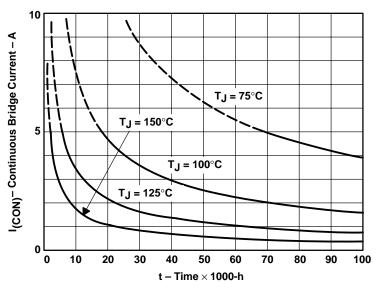


Figure 1. Electromigration Reliability Data

Example:

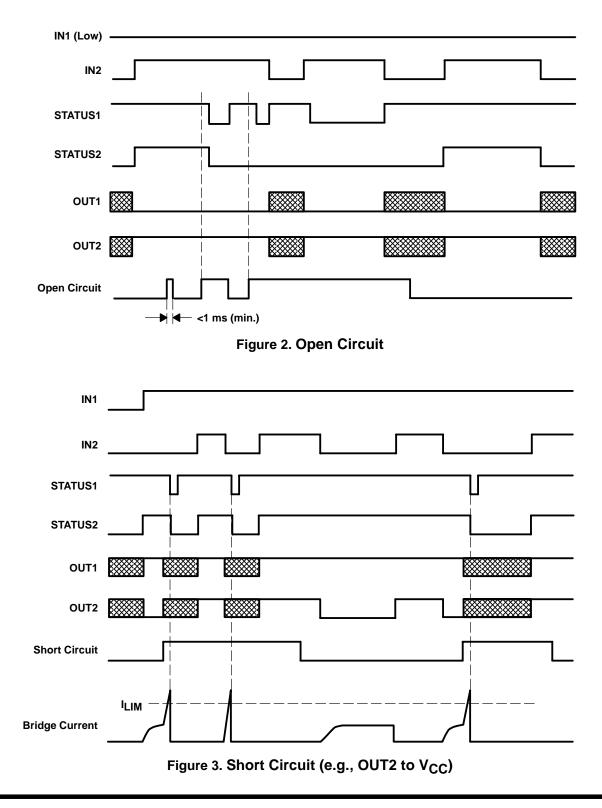
Average continuous bridge current, ICON	Average junction temperature, TJ	Operating lifetime of device based on electromigration
2 A	125°C	>20,000 h
3 A	125°C	>10,000 h



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PARAMETER MEASUREMENT INFORMATION

operating wave forms

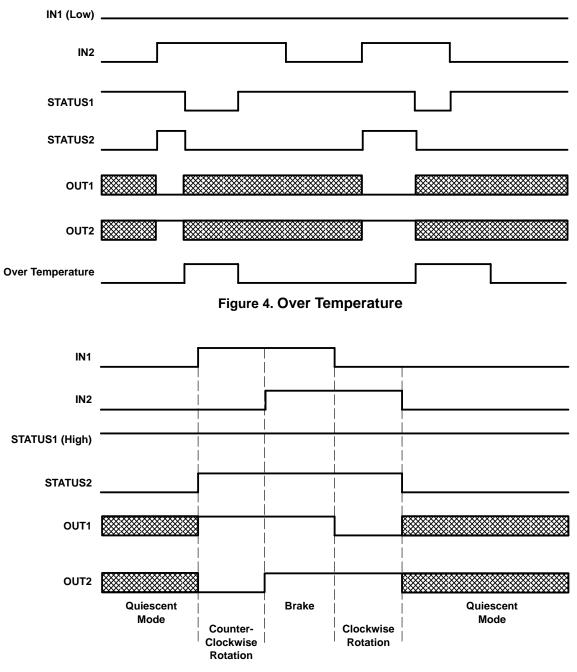


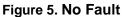


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PARAMETER MEASUREMENT INFORMATION

operating wave forms (continued)







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PRINCIPLES OF OPERATION

protective functions and diagnostics[†]

over current/short circuit‡

The TPIC0108B detects shorts to V_{CC} , ground, or across the load being driven, by comparing the V_{DS} voltage drop across the DMOS outputs against the threshold voltage. The DMOS outputs of the TPIC0108B will be disabled and the fault flags will be generated 10 μ s after an over-current or short-circuit fault is detected. This 10 μ s delay is long enough to serve as a de-glitch filter for high current transients, yet short enough to prevent damage to the DMOS outputs. The DMOS outputs remain latched off until either IN1 or IN2 input is toggled.

In cases where the outputs have a continuous short-to-ground or when enabled from quiescent mode with a short-to-ground already exists (current rise time faster than 0.5 A/ μ s in both instances), the over-current shutdown threshold will decrease to 3 A to reduce power dissipation. This reduction to 3 A is achieved since the DMOS outputs will not be fully enhanced when the over-current threshold is reached if the current rise time exceeds 0.5 A/ μ s. Over-current and/or short-circuit protection is provided up to V_{CC} = 16.5 V and a junction temperature of 90°C.

over temperature

The TPIC0108B disables all DMOS outputs and the fault flags will be set when $T_J \ge 140^{\circ}C$ (min.). The DMOS outputs remain latched off until either IN1 or IN2 input is toggled.

under voltage

The TPIC0108B disables all DMOS outputs when $V_{CC} \leq V_{(UVCC)}$. The outputs will be re-enabled when $V_{CC} \geq V_{(UVCC)}$. No fault flags are set when under-voltage lockout occurs.

over voltage

In order to protect the DMOS outputs from damage caused by excessive supply voltage, the TPIC0108B disables all outputs when $V_{CC} \ge V_{(OVCC)}$. Once $V_{CC} \le V_{(OVCC)}$, either IN1 or IN2 input must be toggled to re-enable the DMOS outputs.

cross conduction

Monitoring circuitry for each transistor detects whether the particular transistor is active to prevent the HSD or LSD of the corresponding half H-bridge from conducting.

open circuit

During operation, the bridge current is controlled continuously. If the bridge current is >10 mA (min.) for a period >1 ms (min.), the fault flags are set. However, the output transistors will not be disabled.

[‡] If a short circuit occurs (i.e., the over-current detection circuitry is activated) at a supply voltage higher than 16.5 V and a junction temperature higher than 90°C, damage to the device may occur.



[†] All limits mentioned are typical values unless otherwise noted.

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PRINCIPLES OF OPERATION

FLAG	IN1	IN2	OUT1	OUT2	STATUS1 [†]	STATUS2
	0	0	Z	Z	1	0‡
Normal operation	0	1	LS HS	-	1	1
	1	0 1	HS	HS	Z 1 HS 1 LS 1	1
	0	0	Z	Z	1	0‡
Open circuit between OUT1 and OUT2	0	1	LS		Ŭ	0
		0	HS		0	0
	1	1	HS	-	1	1
Short circuit from OUT1 to OUT2 (see Notes 7 and 8)	0	1	X		-	0
	1	0	Х	X	0	0
Short circuit from OLIT1 to GND (see Notes 7 and 8)	1	0	Х		0	0
Short circuit norm OOT 1 to OND (See Notes 7 and 6)	1	1	Х	Х	0	0
Chart circuit from OUT2 to CND (and Nation 7 and 9)	0	1	Х	Х	0	0
Short circuit from OOT2 to GND (see Notes 7 and 8)	1	1	Х	Х	0	0
Short circuit from OUT1 to V_{CC} (see Notes 7 and 8)	0	1	Х	Х	0	0
Short circuit from OUT2 to V_{CC} (see Notes 7 and 8)	1	0	Х	Х	0	0
	0	0	Z	Z	1	0‡
Over temperature (see Note 9)	0	1	Z		0	0
	1	0	Z		0	0
	1	1	Z	Z	0	0

DIAGNOSTICS TABLE (see Note 6)

[†] When wired with a pull-up resistor

[‡] In quiescent mode, STATUS2 is pulled down to GND via an internal resistor.

SYMBOL VALUE

0 Logic low

- 1 Logic high
- HS High-side MOSFET conducting

LS Low-side MOSFET conducting

Z No output transistors conducting

X Voltage level undefined

NOTES: 6. All input combinations not stated result in STATUS output = 1.

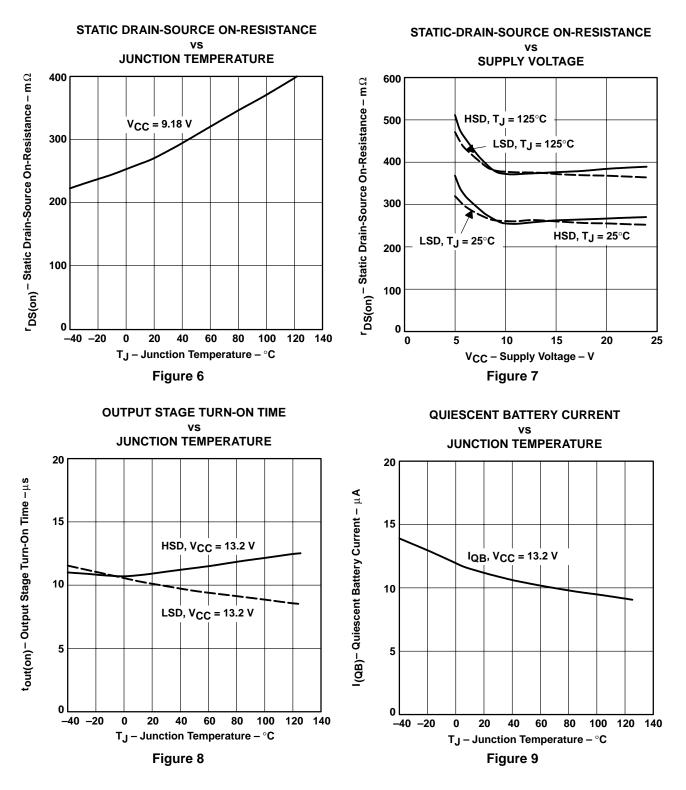
7. STATUS1 active for a minimum of 3 μs.

8. STATUS2 active until an input is toggled.

9. Quiescent current consumption can occur only when the temperature drops below the thermal switch-off temperature.



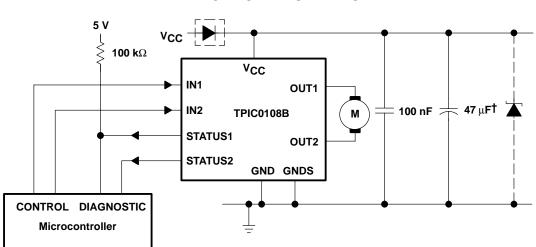
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TYPICAL CHARACTERISTICS



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APPLICATION INFORMATION

⁺ Necessary for isolating supply voltage or interruption (e.g., 47 μF). NOTE: If a STATUS output is not connected to the appropriate microcontroller input, it shall remain unconnected.

recirculation current mode

When an inductive load (motor) is switched from one control mode to another, (i.e., forward to reverse) the TPIC0108B automatically enters a special recirculation current mode condition. This condition allows fast elimination of the recirculation currents caused by inductive switching. Once these currents have subsided to an acceptable level, the device automatically enters the requested state. This feature eliminates the need for either internally or externally connected free wheeling diodes and protects the TPIC0108B from damage due to high inductive voltage transients.

The recirculation current mode condition is triggered when the voltage at the HSD output voltage exceeds typically V_{CC} + 0.7 V. In this condition, a diode inherent in the HSD structure turns on. Simultaneously internal control circuitry turns on the opposite HSD, thus providing a current path for the recirculating currents.

Using TPIC0108B in PWM operation brake mode shall be applied before going into quiescent mode.

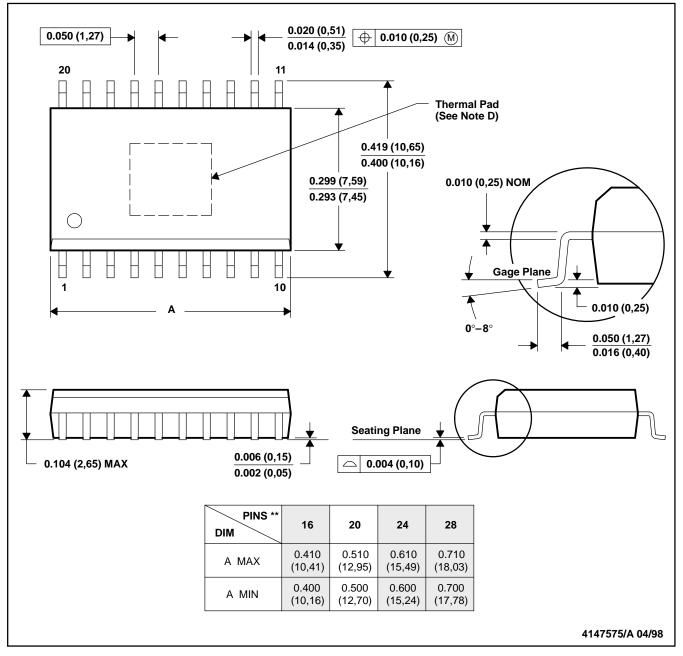


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MECHANICAL DATA

PowerPAD[™] PLASTIC SMALL-OUTLINE PACKAGE

DWP (R-PDSO-G**) 20 PINS SHOWN



NOTES: A. All linear dimensions are in inches (millimeters).

B. This drawing is subject to change without notice.

C. Body dimensions do not include mold flash or protrusion not to exceed 0.006 (0,15).

D. The package thermal performance may be enhanced by bonding the thermal pad to an external thermal plane. This pad is electrically and thermally connected to the backside of the die and possibly selected leads.

PowerPAD is a trademark of Texas Instruments Incorporated.

PACKAGING INFORMATION

Orderable Device	Status ⁽¹⁾	Package Type	Package Drawing	Pins	Package Qty	Eco Plan ⁽²⁾	Lead/Ball Finish	MSL Peak Temp ⁽³⁾
TPIC0108BDWP	ACTIVE	SO Power PAD	DWP	20	25	TBD	CU NIPDAU	Level-3-235C-168 HR
TPIC0108BDWPR	ACTIVE	SO Power PAD	DWP	20	2000	TBD	CU NIPDAU	Level-3-235C-168 HR

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

⁽²⁾ Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details. **TBD:** The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

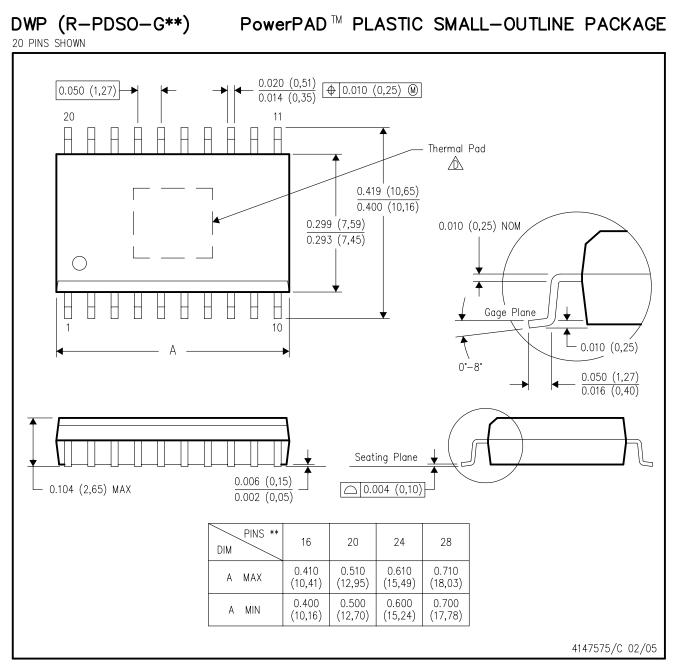
Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

⁽³⁾ MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

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NOTES: A. All linear dimensions are in inches (millimeters).

B. This drawing is subject to change without notice.

C. Body dimensions do not include mold flash or protrusion not to exceed 0.006 (0,15).

This package is designed to be soldered to a thermal pad on the board. Refer to Technical Brief, PowerPad Thermally Enhanced Package, Texas Instruments Literature No. SLMA002 for information regarding recommended board layout. This document is available at www.ti.com http://www.ti.com. See the product data sheet for details regarding the exposed thermal pad dimensions.

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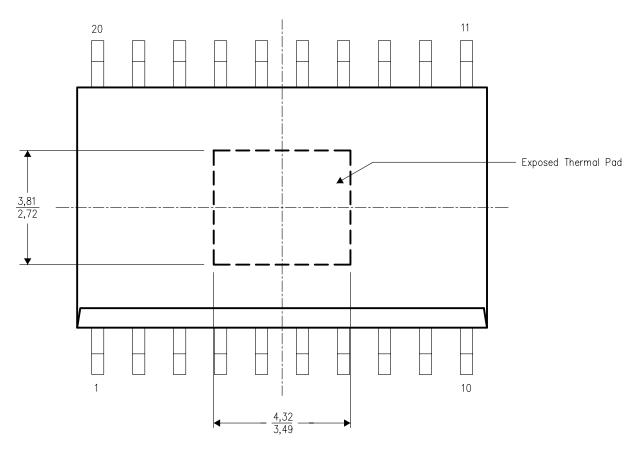


THERMAL INFORMATION

This PowerPAD^M package incorporates an exposed thermal pad that is designed to be attached directly to an external heatsink. When the thermal pad is soldered directly to the printed circuit board (PCB), the PCB can be used as a heatsink. In addition, through the use of thermal vias, the thermal pad can be attached directly to a ground plane or special heatsink structure designed into the PCB. This design optimizes the heat transfer from the integrated circuit (IC).

For additional information on the PowerPAD package and how to take advantage of its heat dissipating abilities, refer to Technical Brief, PowerPAD Thermally Enhanced Package, Texas Instruments Literature No. SLMA002 and Application Brief, PowerPAD Made Easy, Texas Instruments Literature No. SLMA004. Both documents are available at www.ti.com.

The exposed thermal pad dimensions for this package are shown in the following illustration.





NOTE: All linear dimensions are in millimeters

Exposed Thermal Pad Dimensions

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